**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protected

## 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	-	300	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	190	mA
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 100 mA; $T_j$ = 25 °C		-	3	4.5	Ω

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



**60 V, single N-channel Trench MOSFET** 

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S 017aaa255

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX7002AK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
NX7002AK	%CM

[1] % = placeholder for manufacturing site code

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## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
gate-source voltage			-20	20	V
drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	300	mA
	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	190	mA
	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	120	mA
peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	760	mA
total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	265	mW
		[1]	-	325	mW
	T <sub>sp</sub> = 25 °C		-	1330	mW
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
diode					
source current	T <sub>amb</sub> = 25 °C	[1]	-	190	mA
	drain-source voltage gate-source voltage drain current  peak drain current total power dissipation  junction temperature ambient temperature storage temperature diode	$ \begin{array}{lll} drain\text{-source voltage} & T_j = 25 \ ^\circ\text{C} \\ \\ gate\text{-source voltage} \\ \\ drain current & V_{GS} = 10 \ \text{V}; \ T_{sp} = 25 \ ^\circ\text{C} \\ \hline V_{GS} = 10 \ \text{V}; \ T_{amb} = 25 \ ^\circ\text{C} \\ \hline V_{GS} = 10 \ \text{V}; \ T_{amb} = 100 \ ^\circ\text{C} \\ \hline peak drain current & T_{amb} = 25 \ ^\circ\text{C}; single pulse; \ t_p \leq 10 \ \mu\text{s} \\ \hline total power dissipation & T_{amb} = 25 \ ^\circ\text{C} \\ \hline Junction temperature & \\ ambient temperature & \\ storage temperature & \\ \\ \hline \end{diode} $	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \\ \text{drain current} \\ \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \text{drain current} \\ \end{array} \begin{array}{c} V_{GS} = 10 \text{ V};  T_{sp} = 25  ^{\circ}\text{C} \\ \hline V_{GS} = 10 \text{ V};  T_{amb} = 25  ^{\circ}\text{C} \\ \hline V_{GS} = 10 \text{ V};  T_{amb} = 100  ^{\circ}\text{C} \\ \hline V_{GS} = 10 \text{ V};  T_{amb} = 100  ^{\circ}\text{C} \\ \hline 11 \\ \hline 1 \\ \hline$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

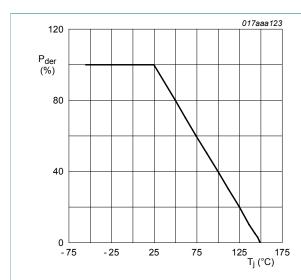


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

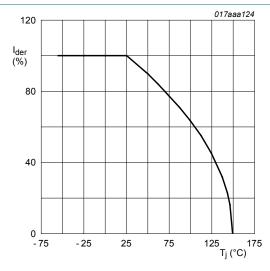


Fig. 2. Normalized continuous drain current as a function of junction temperature

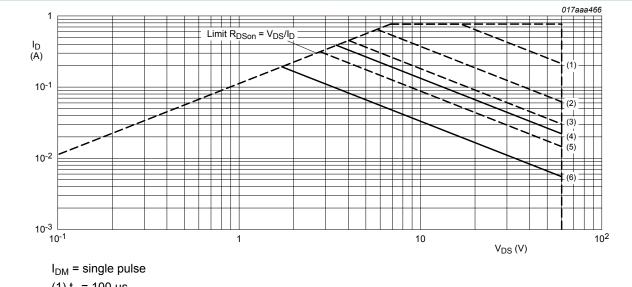
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

NX7002AK

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### 60 V, single N-channel Trench MOSFET



(1)  $t_p = 100 \mu s$ 

(2)  $t_p = 1 \text{ ms}$ 

(3)  $t_p = 10 \text{ ms}$ 

(4) DC;  $T_{sp}$  = 25 °C

 $(5) t_p = 100 \text{ ms}$ 

(6) DC;  $T_{amb}$  = 25 °C; drain mounting pad 1 cm<sup>2</sup>

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	410	470	K/W
			[2]	-	330	380	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	95	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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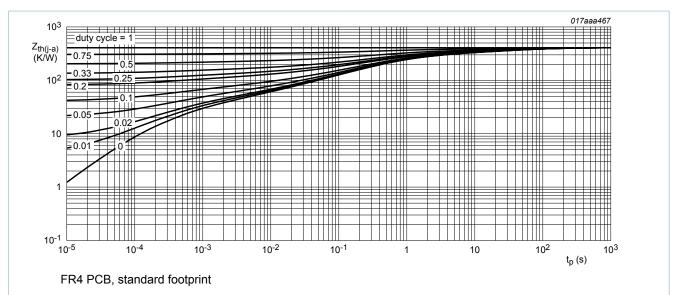


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

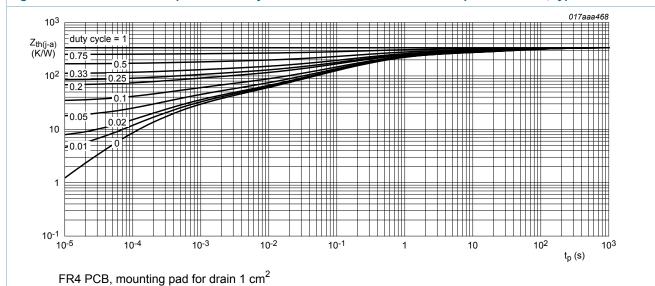


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

**60 V, single N-channel Trench MOSFET** 

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.5	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.5	μA
		V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
200	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	3	4.5	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 150 °C	-	6.2	9.2	Ω
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	3.7	5.2	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	500	-	mS
Dynamic cl	haracteristics		·			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 4.5 V;	-	0.33	0.43	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.09	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	15	20	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	3.4	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	2	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 40 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 10 V;	-	6	12	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	11	20	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-dra	in diode		ı	1	1	,
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	0.47	0.8	1.2	V

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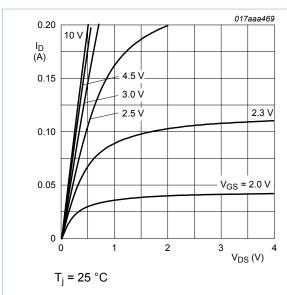
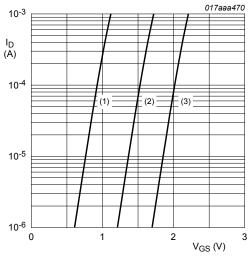


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

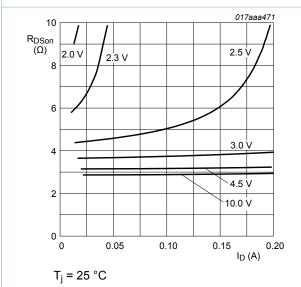
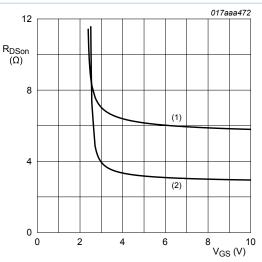


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



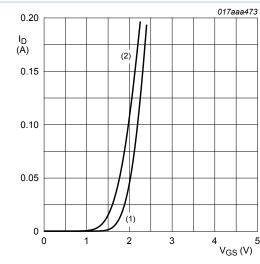
 $I_D = 0.2 A$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, single N-channel Trench MOSFET



 $V_{DS} > I_D \times R_{DSon}$ (1)  $T_i = 25 \, ^{\circ}C$ 

(2)  $T_i = 150 \,^{\circ}\text{C}$ 

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

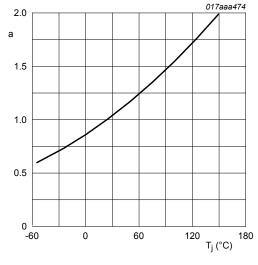
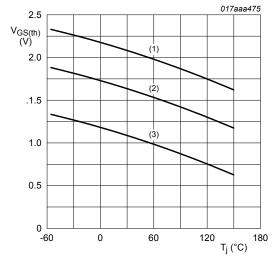


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

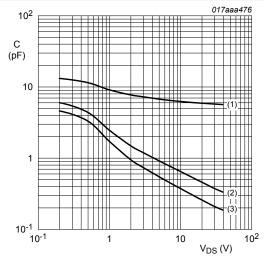
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D$  = 0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### **60 V, single N-channel Trench MOSFET**

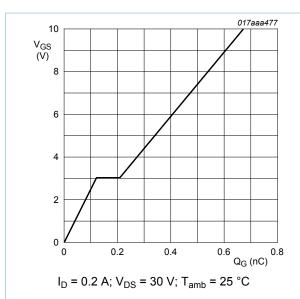


Fig. 14. Gate-source voltage as a function of gate charge; typical values

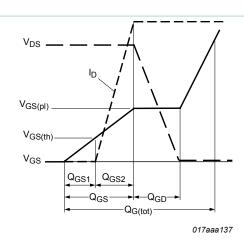
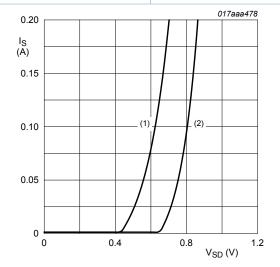


Fig. 15. MOSFET transistor: Gate charge waveform definitions



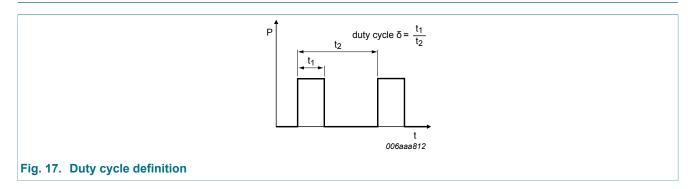
 $V_{GS} = 0 V$ (1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 16. Source current as a function of source-drain voltage; typical values

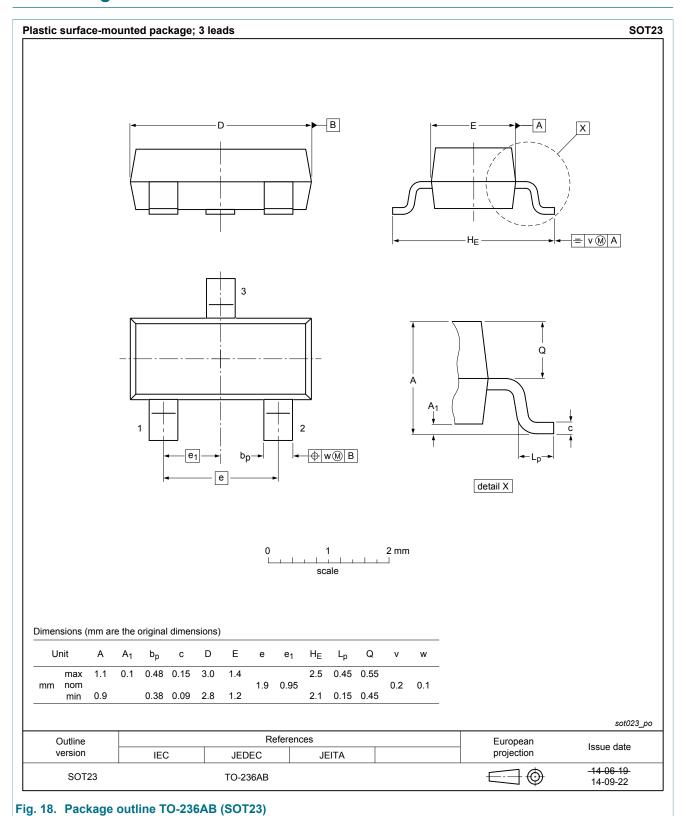
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## 11. Test information



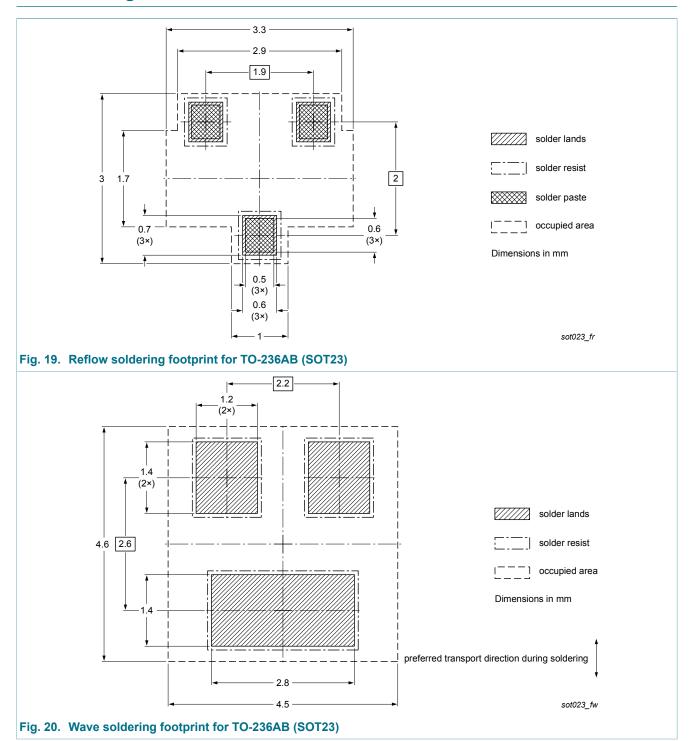
**60 V, single N-channel Trench MOSFET** 

## 12. Package outline



**60 V, single N-channel Trench MOSFET** 

## 13. Soldering



**60 V, single N-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002AK v.7	20150806	Product data sheet	-	NX7002AK v.6
Modifications:	Dynamic parar	meters updated		
NX7002AK v.6	20150521	Product data sheet	-	NX7002AK v.5
NX7002AK v.5	20130213	Product data sheet	-	NX7002AK v.4
NX7002AK v.4	20121213	Product data sheet	-	NX7002AK v.3
NX7002AK v.3	20120710	Product data sheet	-	NX7002AK v.2
NX7002AK v.2	20120301	Product data sheet	-	NX7002AK v.1
NX7002AK v.1	20120212	Product data sheet	-	-

#### 60 V, single N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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